

# AN8801SC

## Three-Beam Method Head Amplifier IC for CD Player

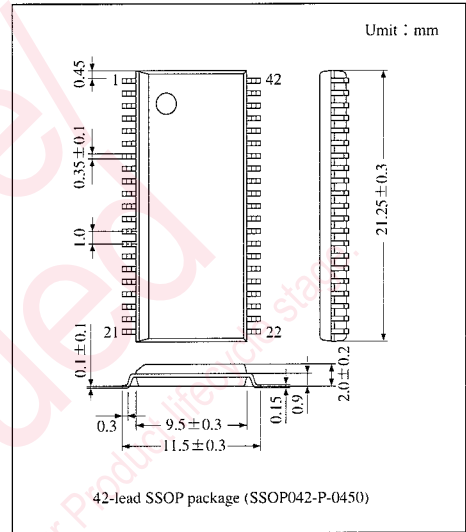
### ■ Overview

The AN8801SC is a head amplifier IC supporting a digital servo.

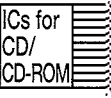
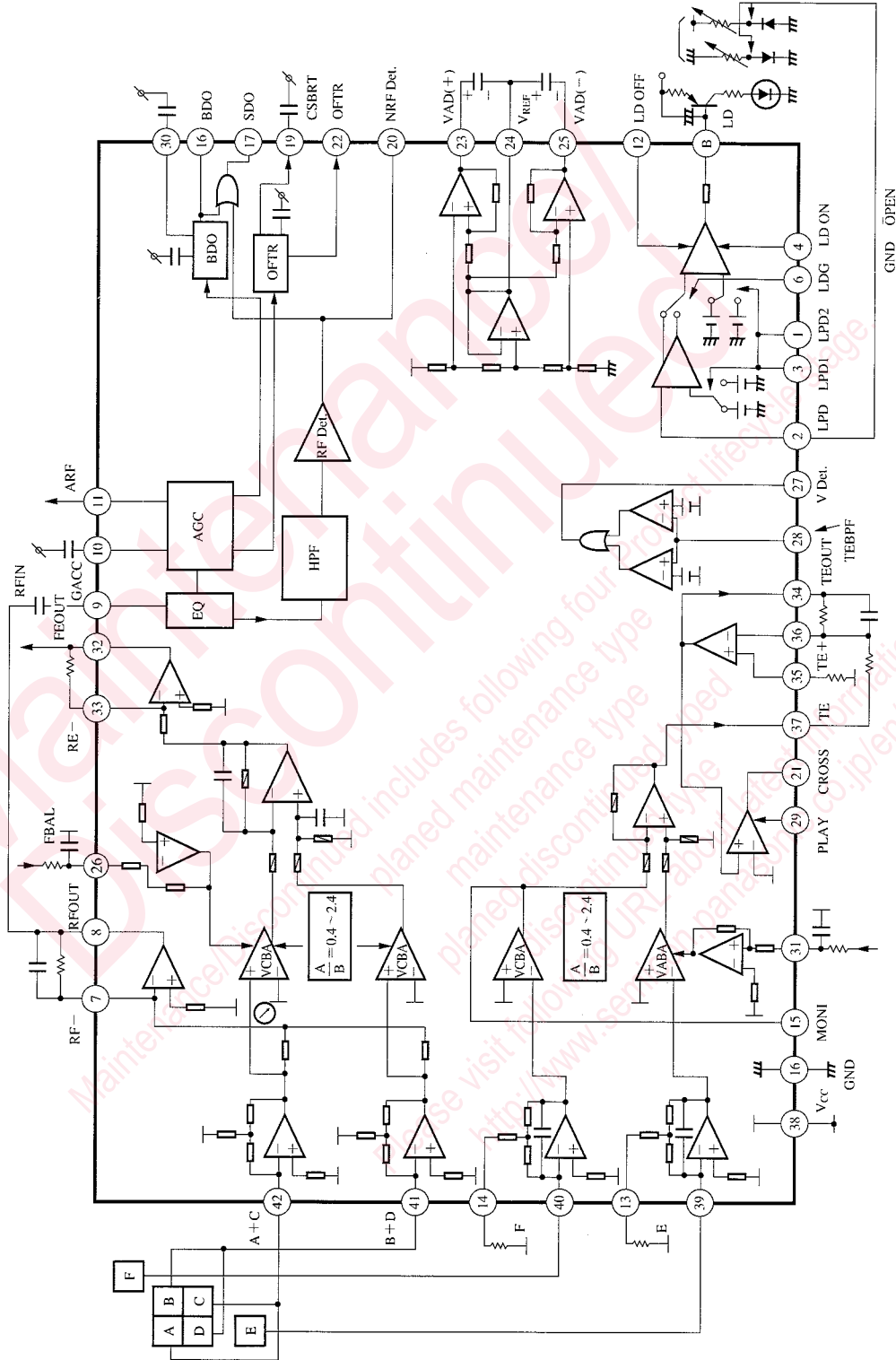
Combination of this IC and the MN6650 (digital servo processor) allows the rational servo system to be constructed with small number of external parts.

### ■ Features

- 5V single supply operation
- Low consumption power
- I-V amplifier, tracking error amplifier, focus error amplifier, RF amplifier and APC built-in
- Detection of DO, CROSS, OFTR and vibration
- Combination with the MN6650 enabling automatic adjustment for tracking balance, tracking offset, tracking gain, focus offset and focus gain



■ Block Diagram



## ■ Pin Description

Pin No.	Pin Name	I/O	Function Description
1	LDP1	I	Polarity switching of APC monitor P <sub>D</sub> (1)
2	LPD	I	Signal input of P <sub>D</sub> for LD output monitor
3	LDP2	I	Polarity switching of APC monitor P <sub>D</sub> (2)
4	LDON	I	ON/OFF switching of LD APC
5	LD	O	Connected to base of external Tr for LD drive
6	LDG	I	APC loop gain switching
7	RF--	I	Reverse rotation input pin of RF Amp. for connecting a resistance
8	RFOUT	O	Output pin of RF Amp. (reverse rotation amp.)
9	RFIN	I	RF AGC input pin
10	C. AGC	—	C connecting pin for RF AGC loop filter
11	ARF	O	RF output pin after AGC
12	LDOFF	I	Input pin for forced stop of LD APC
13	PDER	—	Connecting pin for resistance setting IV conversion resistance value of PIN diode E
14	PDFR	—	Connecting pin for resistance setting IV conversion resistance value of PIN diode F
15	MONI	—	Output monitor pin of TE balance amp. (F)
16	GND	—	Ground pin
17	SDO	O	SDO detection output pin ; positive logic ; SDO=BDO+NRFDET
18	BDO	O	BDO detection output pin ; positive logic
19	C. SBRT	—	Connecting pin C for OFTR low speed detection
20	NRFDET	O	Amplitude detection information of RF signal; negative logic
21	CROSS	O	Output of TE CROSS detection signal
22	OFTR	O	OFF TRACK detection output
23	VAD (+)	O	V <sub>CC</sub> ×0.8 (V) output pin
24	V <sub>REF</sub>	O	V <sub>CC</sub> ×0.5 (V) output pin
25	VAD (-)	O	V <sub>CC</sub> ×0.2 (V) output pin
26	FBAL	I	Control signal input pin for FO balance adjustment
27	VDET	O	Output of vibration detection
28	TEBPF	I	Input of vibration detection
29	PLAY	I	PLAY signal pin ; positive logic
30	C. SBDO	—	Connecting pin C for low speed detection of dark level DO
31	TBAL	I	Control signal input pin for TE balance adjustment
32	FEOUT	O	Output pin of focus error signal
33	FE-	I	Reverse rotation input pin of FE Amp.
34	TEOUT	O	Output pin of TE Amp.
35	TE+	I	Normal rotation input pin of TE Amp.
36	TE-	I	Reverse rotation input pin of TE Amp.
37	TE	O	Output pin of TE signal
38	V <sub>CC</sub>	—	Supply connecting pin
39	PDE	I	Connected to PIN diode E
40	PDF	I	Connected to PIN diode F
41	PDAC	I	Connected to B/D of astigmatic 4-division P <sub>D</sub>
42	PDBD	I	Connected to A/C of astigmatic 4-division P <sub>D</sub>

### ■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Unit
Supply Voltage	V <sub>CC</sub>	6	V
Supply Current	I <sub>CC</sub>	50	mA
Power Dissipation	P <sub>D</sub>	300	mW
Operating Ambient Temperature	T <sub>opr</sub>	-30 ~ +85	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +125	°C

### ■ Recommended Operating Range (Ta=25°C)

Parameter	Symbol	Range
Operating Supply Voltage Range	V <sub>CC</sub>	4.5V ~ 5.5V

### ■ Electrical Characteristics (Ta=25°C ± 2°C)

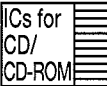
Parameter	Symbol	Condition	min.	typ.	max.	Unit
Total Circuit Current	I <sub>tot</sub>	V <sub>CC</sub> =5V	10	14.5	19	mA
V <sub>REF</sub> Output Voltage	V <sub>REF</sub>	V <sub>CC</sub> =5V	2.25	2.53	2.81	V
VAD (+) Output Voltage	ΔV <sub>AD(+)</sub>	V <sub>CC</sub> =5V	1.28	1.43	1.58	V
VAD (-) Output Voltage	ΔV <sub>AD(-)</sub>	V <sub>CC</sub> =5V	1.30	1.45	1.60	V

#### Focus Error Amp.

Output Offset Voltage of Focus Error Amp.	V <sub>OF-FO</sub>	V <sub>CC</sub> =5V	-300	0	300	mV
Crosstalk Quantity of Focus Error Offset Balance	V <sub>OF-FOB</sub>	V <sub>CC</sub> =5V, V <sub>FB</sub> =0.5V Applied	-250	—	250	mV
I-V Conversion Gain of Focus Error Amp.	R <sub>FO</sub>	V <sub>CC</sub> =5V, V <sub>FB</sub> =V <sub>REF</sub>	80	115	150	kΩ
I-V Conversion Relative Gain of Focus Error Amp.	ΔR <sub>FO</sub>	V <sub>CC</sub> =5V, V <sub>FB</sub> =V <sub>REF</sub>	-10	0	10	%
Focus Balance Variable Range 1-1	B <sub>F01-1</sub>	V <sub>CC</sub> =5V, V <sub>FB</sub> =5V	0.35	0.5	0.65	—
Focus Balance Variable Range 1-2	B <sub>F01-2</sub>	V <sub>CC</sub> =5V, V <sub>FB</sub> =0V	1.05	1.5	1.95	—
Focus Balance Variable Range 2-1	B <sub>F02-1</sub>	V <sub>CC</sub> =5V, V <sub>FB</sub> =5V	1.05	1.5	1.95	—
Focus Balance Variable Range 2-2	B <sub>F02-2</sub>	V <sub>CC</sub> =5V, V <sub>FB</sub> =0V	0.35	0.5	0.65	—
Frequency Characteristics of Focus Error Amp.	G <sub>FO</sub>	V <sub>CC</sub> =5V, f=1kHz, 30kHz Input	-4.5	-3	-1.5	dB

#### Tracking Error Amp.

Output Offset Voltage of Tracking Error Amp.	V <sub>OF-T</sub>	V <sub>CC</sub> =5V	-300	0	300	mV
Crosstalk Quantity of Tracking Error Offset Balance	V <sub>OF-TB</sub>	V <sub>CC</sub> =5V, V <sub>TB</sub> =0.5V Applied	-250	—	250	mV
I-V Conversion Gain of Tracking Error Amp.	R <sub>T</sub>	V <sub>CC</sub> =5V, V <sub>TB</sub> =V <sub>REF</sub>	540	720	900	kΩ
I-V Conversion Relative Gain of Tracking Error Amp.	ΔR <sub>T</sub>	V <sub>CC</sub> =5V, V <sub>TB</sub> =V <sub>REF</sub>	-10	0	10	%
Tracking Balance Variable Range 1-1	B <sub>T1-1</sub>	V <sub>CC</sub> =5V, V <sub>TB</sub> =5V	0.35	0.5	0.65	—
Tracking Balance Variable Range 1-2	B <sub>T1-2</sub>	V <sub>CC</sub> =5V, V <sub>TB</sub> =0V	1.05	1.5	1.95	—
Tracking Balance Variable Range 2-1	B <sub>T2-1</sub>	V <sub>CC</sub> =5V, V <sub>TB</sub> =5V	1.05	1.5	1.95	—
Tracking Balance Variable Range 2-2	B <sub>T2-2</sub>	V <sub>CC</sub> =5V, V <sub>TB</sub> =0V	0.35	0.5	0.65	—
Frequency Characteristics of Tracking Error Amp.	G <sub>TO</sub>	V <sub>CC</sub> =5V, f=3kHz, 46kHz Input	-4.5	-3	-1.5	dB



**Electrical Characteristics (Cont.)** ( $T_a = 25^\circ\text{C} \pm 2^\circ\text{C}$ )

Parameter	Symbol	Condition	min.	typ.	max.	Unit
<b>CROSS Detection</b>						
CROSS Output H Level	$V_{CR-H}$	$V_{CC}=5V, V_{TB}=V_{REF}$ Input : $f=3\text{kHz}$	4.2	—	—	V
CROSS Output L Level	$V_{CR-L}$	$V_{CC}=5V, V_{TB}=V_{REF}$ Input : $f=3\text{kHz}$	—	—	0.8	V
PLAY mode CROSS Operation	$V_{CR-P}$	$V_{CC}=5V, V_{TB}=V_{REF}$ Input : $f=3\text{kHz}$	4.2	—	—	V
<b>RF-Amp.</b>						
RF-Amp. Offset Voltage	$V_{OF-RF}$	$V_{CC}=5V$	-75	0	75	mV
RF-Amp. I-V Conversion Gain	$R_{RF}$	$V_{CC}=5V$	44.5	56	67.5	k $\Omega$
RF-Amp. I-V Conversion Relative Gain	$\Delta R_{RF1}$	$V_{CC}=5V$	-10	0	10	%
RF-Amp. Frequency Characteristics <small>Note)</small>	$G_{RF}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, 3\text{MHz}$	-4.5	-3	-1.5	dB
<b>AGC</b>						
AGC Max. Gain	$G_{AGC}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, \text{Sine Wave}$	15	18.5	21	dB
EQ Characteristics	$\Delta G_{EQ}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, \text{Sine Wave}$	0	1.0	2.0	dB
AGC Operation Gain	$G_{OP-AGC}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, \text{Sine Wave}$	4	6	9	dB
AGC Compressibility	$G_{cm-AGC}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, \text{Sine Wave}$	0	2	3.5	dB
AGC Frequency Characteristics	$G_{f-AGC}$	$V_{CC}=5V$ Input : $f=3\text{MHz}, \text{Sine Wave}$	-1.5	0	2.5	dB
<b>RFDET</b>						
RFDET Detection Operation	$V_{NRF}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, \text{Sine Wave}$	75	115	155	mV <sub>P-P</sub>
RFDET H Level	$V_{NRF-H}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, \text{Sine Wave}$	4.2	—	—	V
RFDET L Level	$V_{NRF-L}$	$V_{CC}=5V$ Input : $f=500\text{kHz}, \text{Sine Wave}$	—	—	0.8	V
<b>BDO</b>						
BDO Detection Current	$I_{BDO}$	$V_{CC}=5V$	1.0	1.4	1.8	$\mu\text{A}$
BDO H Level	$V_{BDO-H}$	$V_{CC}=5V$ Input : $f=1\text{kHz}, \text{Rectangle Wave}$	4.2	—	—	V
BDO L Level	$V_{BDO-L}$	$V_{CC}=5V$ Input : $f=1\text{kHz}, \text{Rectangle Wave}$	—	—	0.8	V
<b>OFTR</b>						
OFTR Detection Current	$I_{OFTR}$	$V_{CC}=5V$	1.0	1.4	1.8	$\mu\text{A}$
OFTR H Level	$V_{OFTR-H}$	$V_{CC}=5V$ Input : $f=1\text{kHz}, \text{Rectangle Wave}$	4.2	—	—	V
OFTR L Level	$V_{OFTR-L}$	$V_{CC}=5V$ Input : $f=1\text{kHz}, \text{Rectangle Wave}$	—	—	0.8	V
<b>SDO</b>						
SDO H Level	$V_{SDO-H}$	$V_{CC}=5V$ Input : $f=1\text{kHz}, \text{Rectangle Wave}$	4.2	—	—	V
SDO L Level	$V_{SDO-L}$	$V_{CC}=5V$ Input : $f=1\text{kHz}, \text{Rectangle Wave}$	—	—	0.8	V

Note) The value may fluctuate by the influence of printed board, socket and etc.

**Electrical Characteristics (Cont.)** (Ta=25°C ±2°C)

Parameter	Symbol	Condition	min.	typ.	max.	Unit
<b>LD—APC</b>						
LD ON H Input Level	V <sub>LDON-H</sub>	V <sub>CC</sub> =5V	3.5	—	—	V
LD OFF H Input Level	V <sub>LDOFF-H</sub>	V <sub>CC</sub> =5V	3.5	—	—	V
LD ON Operation Voltage (1)	V <sub>LD(1)</sub>	V <sub>CC</sub> =5V, V <sub>2</sub> : DC Sweep	1.9	2.2	2.5	V
LD ON Operation Voltage (2)	V <sub>LD(2)</sub>	V <sub>CC</sub> =5V, V <sub>2</sub> : DC Sweep	0.135	0.17	0.205	V
LD ON Operation Voltage (3)	V <sub>LD(3)</sub>	V <sub>CC</sub> =5V, V <sub>2</sub> : DC Sweep	0.115	0.135	0.155	V
<b>V. Det. Detection</b>						
V. Det. Level (1)	V <sub>Det.(1)</sub>	V <sub>CC</sub> =5V, V <sub>28</sub> : DC Sweep	52	74	96	mV
V. Det. Level (2)	V <sub>Det.(2)</sub>	V <sub>CC</sub> =5V, V <sub>28</sub> : DC Sweep	-95	-73	-51	mV
V. Det. H Level	V <sub>Det.-H</sub>	V <sub>CC</sub> =5V, V <sub>28</sub> : DC Sweep	4.2	—	—	V
V. Det. L Level	V <sub>Det.-L</sub>	V <sub>CC</sub> =5V, V <sub>28</sub> : DC Sweep	—	—	0.8	V

**Operational Description**

**•RF Amplifier**

As shown in Figure 1, RF signals are generated by three-beam method pick-up.

Equivalent resistance to RFOUT (Pin 8) is 58.5k Ω, when resistance between RF and RFOUT is 10k Ω.

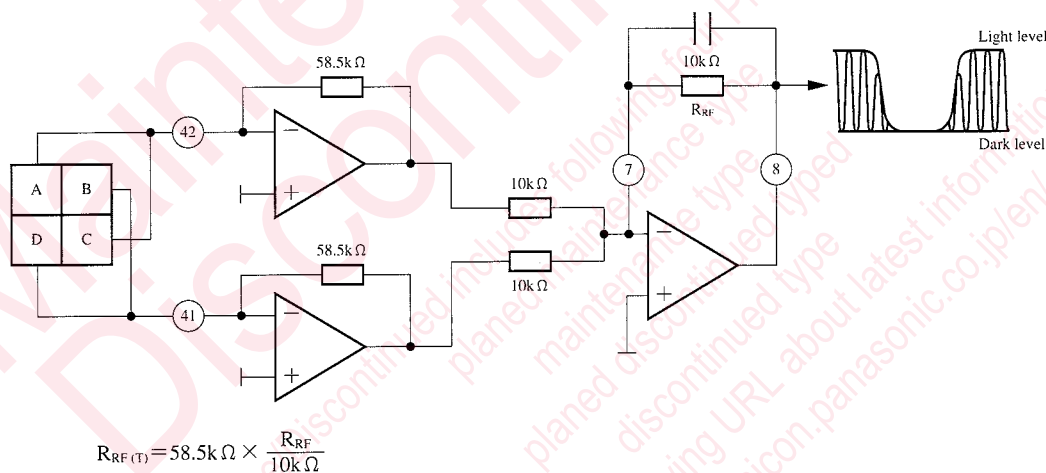
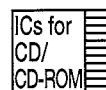


Figure 1 : RF Amplifier

•Focus Error Amplifier

As shown in Figure 2, the operation result of  $(A + C) / (B + D)$  is outputted to FEOUT (Pin 32). Equivalent resistance to FEOUT is  $234k\Omega$ , when resistance between FE and FEOUT is  $40k\Omega$ .

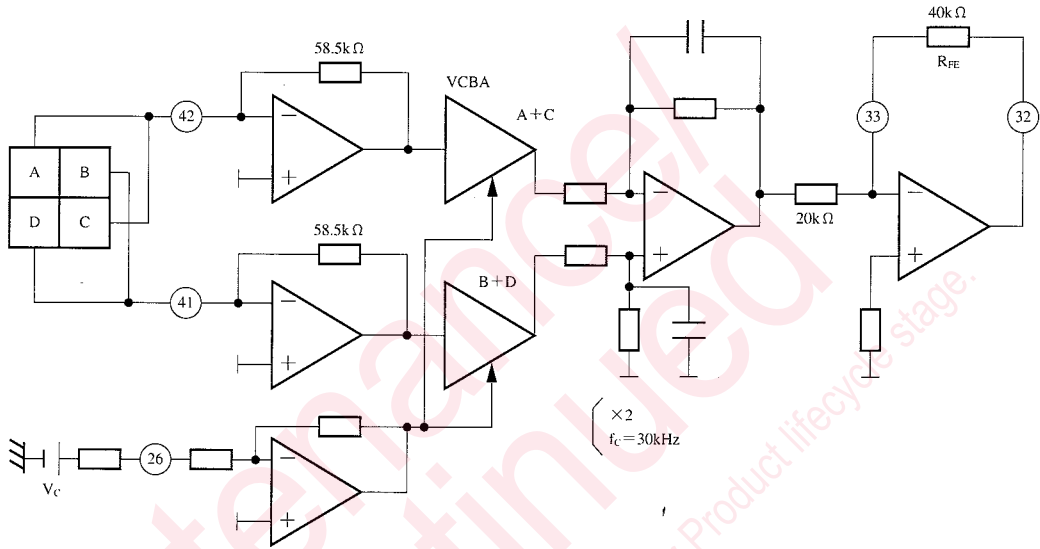


Figure 2 : Focus Error Amplifier

The VCBA is for focus balance adjustment. Connecting  $100k\Omega$  of external resistance to Pin 26, signal ratio between  $A + C$  and  $B + D$  can be controlled as shown in Table 1.

Table 1

$V_c$	$\frac{A+C}{B+D}$	$\frac{B+D}{A+C}$
0V	0.4	2.5
2.5V	1.0	1.0
5.0V	2.5	0.4

•Tracking Error Amplifier

As shown in Figure 3, it receives the output currents E and F of three-beam method pin photo diode for sub-beam detection, and outputs the operation result of  $E - F$  to TEOUT (Pin 34).

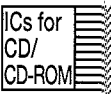
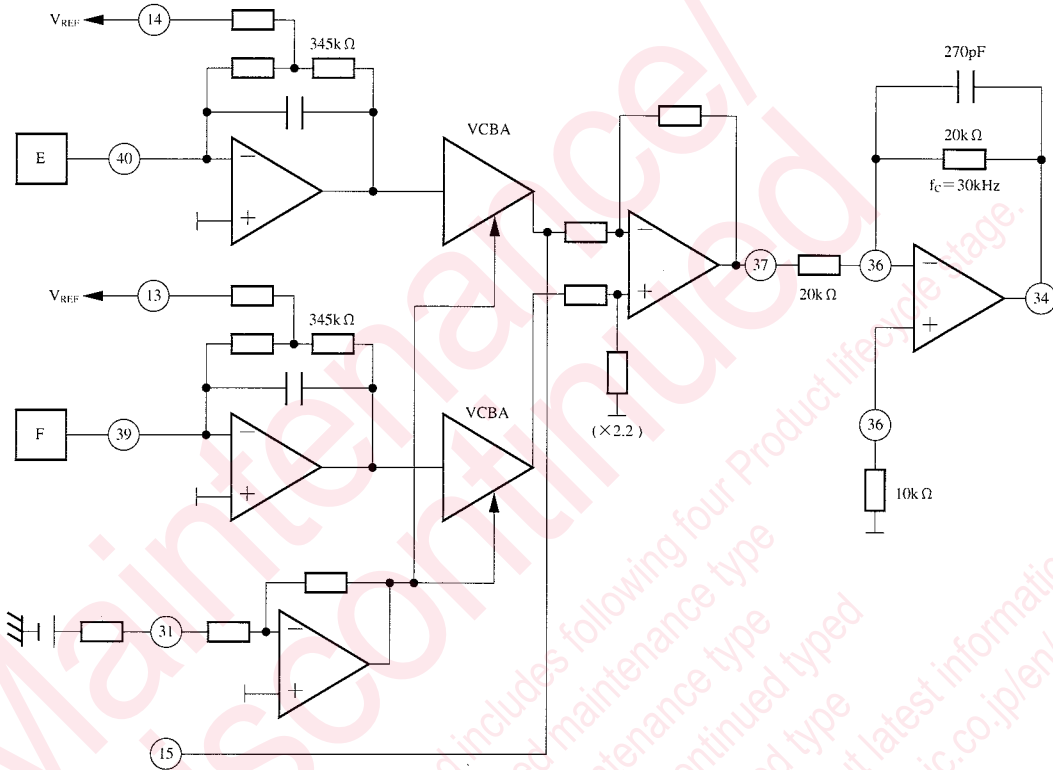


Figure 3 : Tracking Error Amplifier

Pins 13 and 14 are used to make the resistance converting the current to voltage variable. When these pins are directly connected to  $V_{REF}$  and  $20k\Omega$  of resistance is connected between TE and TE-, and between TE and TEOUT respectively, equivalent resistance to TEOUT is  $757k\Omega$ .

Table 2

$V_c$	E/F	F/E
0V	0.4	2.5
2.5V	1.0	1.0
5.0V	2.5	0.4

The VCBA is for tracking balance adjustment in the same way of for focus. Table 2 shows the tracking balance ratio under the same conditions as shown in Table 1. The capacitor connected between TE- and TEOUT must be set so that  $f_c$  can be 30 kHz.



### •AGC

In order to absorb the attenuation of RF signal by disk, pick-up dispersion, finger print and other factors, AGC circuit for RF is incorporated.

The input impedance of Pin⑨ is approx. 27.9k $\Omega$ . By Pin⑪ (ARF), gain-controlled RF-signal is outputted. Input allowable level is approx. 1V<sub>p-p</sub>~500mV<sub>p-p</sub>~250mV<sub>p-p</sub>, and output is 1 V<sub>p-p</sub>. Pin⑩ is a connecting pin with capacity for constructing the AGC loop filter. It is recommended that the external capacitor of 1  $\mu$ F around should be connected for V<sub>CC</sub>.

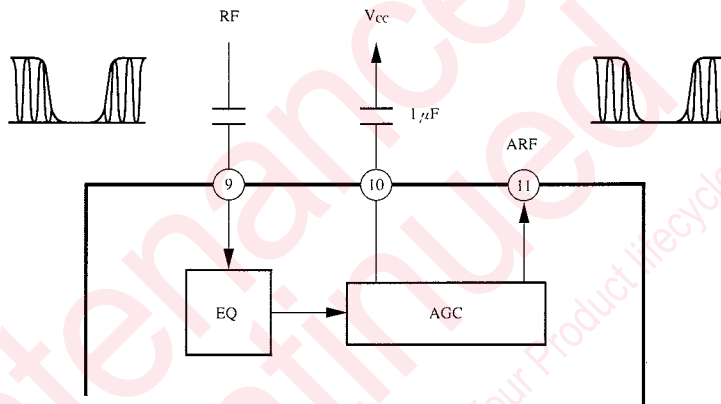


Figure 4 : AGC

### •RFDET

The RFDET detects amplitude of RF signal inputted to Pin⑨. Threshold value is approx. 100mV (f=500kHz), and RFPresent =L, RF Absent =H are outputted.

### •BDO Detection

It detects BDO by the low speed detection circuit and high speed detection circuit. The high speed detection circuit is incorporated. On the other hand, the capacitor of the low speed detection circuit must be connected to Pin⑩. The capacity value is 680pF and it is recommended that it should be connected for V<sub>CC</sub>. When this capacity value of Pin⑩ is increased, BDO is detected with large RF missing rate. When it is decreased, BDO can be detected with small RF missing rate.

BDO present =H

BDO absent =L

### •OFTR Detection

OFTR detection reversely corresponds with BDO detection. However, its detection method is the same as for BDO. Capacitor for the low speed detection must be connected to Pin⑨. It is recommended that it should be connected to V<sub>CC</sub> at 3000 pF in the same way as for Pin⑩. The relation between the capacity value and OFTR detection timing is as the same for BDO.

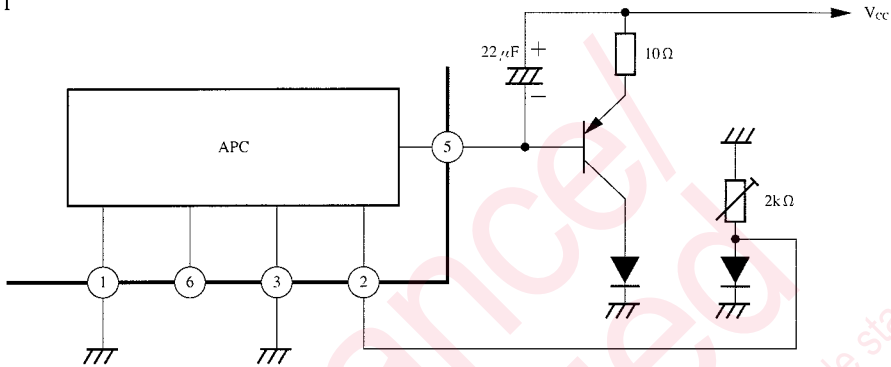
OFTR =H

Off from OFTR =L

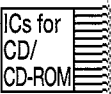
•APC

The APC is constructed to support the P-sub and N-sub of laser PD either.

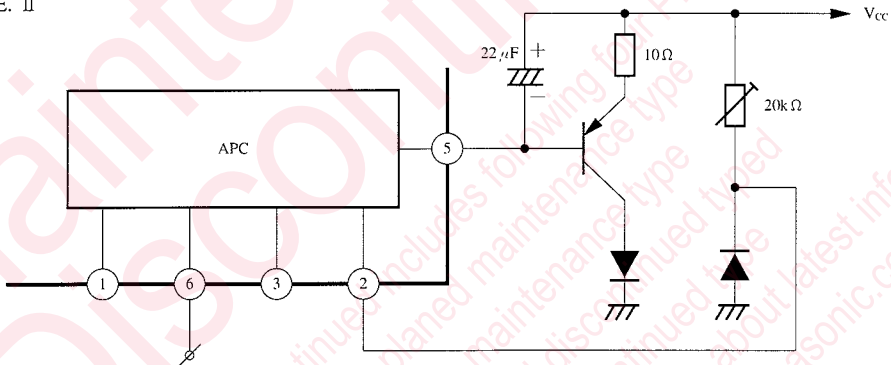
(1) Type I



By connecting Pin① or ③ to GND, the reference voltage of LD can be switched. When Pin① is connected to GND, the reference voltage becomes 170 mV. When Pin③ is connected to GND, it becomes 140 mV.



(2) TYPE. II



•Supply for AD, Reference Supply

Three supplies are incorporated : two supplies for AD ( $V_{CC} \times 0.8$ ,  $V_{CC} \times 0.2$  output) and a servo reference supply ( $V_{CC}/2$ ). Pin② outputs  $V_{CC} \times 0.8$  and Pin⑤ outputs  $V_{CC} \times 0.2$ , respectively. Pin② has approx. 2mA of capacity only for source, and Pin⑤ has approx. 2mA of capacity only for sink. A capacitor for oscillation prevention is required for VREF. It is recommended that the capacitor value should be  $1 \mu F$  to  $100 \mu F$ . Also, Pin④ outputs  $V_{CC}/2$ , and has approx. 3mA of current capacity for sink/source. It is recommended that it should be given  $1 \mu F$  to  $10 \mu F$  of capacity in addition.

•Vibration Detection

The AN8801SC has a wind comparator of approx.  $\pm 70mV$ . Abnormal vibration components of tracking error are detected and the data for whether vibration is present or not is outputted to Pin⑦.

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